WeEn Semiconductors

SCR

BT151-1000RT

| Symbol | Parameter | Conditions | Min | Тур | Max | Unit |
|---------------------|-----------------------------------|---|-----|-----|-----|------|
| dV _D /dt | rate of rise of off-state voltage | V_{DM} = 670 V; T_j = 150 °C; (V_{DM} = 67% of V_{DRM}); exponential waveform; gate open circuit; Fig. 12 | - | 300 | - | V/µs |

5. Pinning information

Table 2. Pinning information

| Pin | Symbol | Description | Simplified outline | Graphic symbol |
|-----|--------|-----------------------------------|--------------------|------------------------|
| 1 | K | cathode | mb | А - [-] - К |
| 2 | А | anode | | G sym037 |
| 3 | G | gate | | Symosi |
| mb | A | mounting base; connected to anode | | |
| | | | TO-220AB (SOT78) | |

6. Ordering information

Table 3. Ordering information

| Type number | Package | | | | | |
|--------------|----------|--|---------|--|--|--|
| | Name | Description | Version | | | |
| BT151-1000RT | TO-220AB | plastic single-ended package; heatsink mounted; 1 mounting hole; 3-lead TO-220AB | SOT78 | | | |

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7. Limiting values

Table 4. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

| | | Max | Unit |
|---|-----------|------|------|
| V _{DRM} repetitive peak off-state voltage | - | 1000 | V |
| V _{RRM} repetitive peak reverse voltage | - | 1000 | V |
| I _{T(AV)} average on-state current half sine wave; T _{mb} ≤ 134 °C | - | 7.5 | Α |
| $I_{T(RMS)}$ RMS on-state current half sine wave; $T_{mb} \le 134$ °C; Fig. 1 Fig. 2; Fig. 3 | <u>1;</u> | 12 | Α |
| I_{TSM} non-repetitive peak onstate current half sine wave; $T_{j(init)} = 25$ °C; $t_p = 10$ | 0 ms; - | 120 | Α |
| half sine wave; $T_{j(init)} = 25 ^{\circ}\text{C}$; $t_p = 8$. | .3 ms - | 132 | Α |
| I^2 t I ² t for fusing $t_p = 10 \text{ ms; SIN}$ | - | 72 | A²s |
| dI_T/dt rate of rise of on-state $I_G = 30 \text{ mA}$ current | - | 50 | A/µs |
| I _{GM} peak gate current | - | 2 | Α |
| V _{RGM} peak reverse gate voltage | - | 5 | V |
| P _{GM} peak gate power | - | 5 | W |
| P _{G(AV)} average gate power over any 20 ms period | - | 0.5 | W |
| T _{stg} storage temperature | -40 | 150 | °C |
| T _j junction temperature | - | 150 | °C |

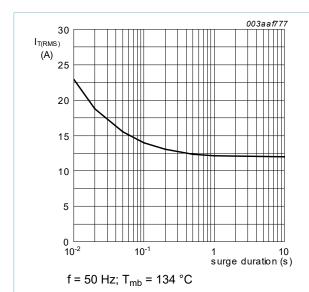


Fig. 1. RMS on-state current as a function of surge duration; maximum values

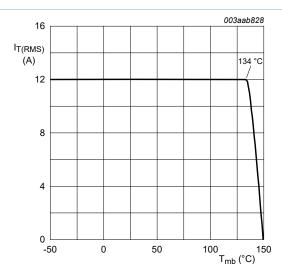


Fig. 2. RMS on-state current as a function of mounting base temperature; maximum values

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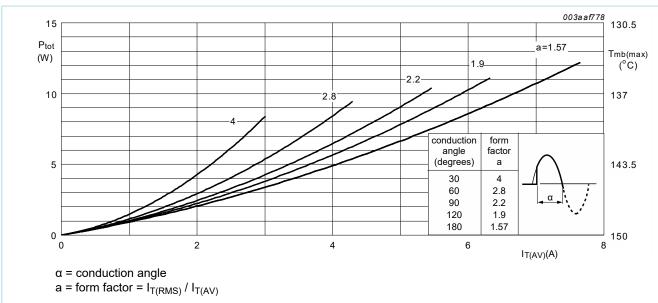


Fig. 3. Total power dissipation as a function of average on-state current; maximum values

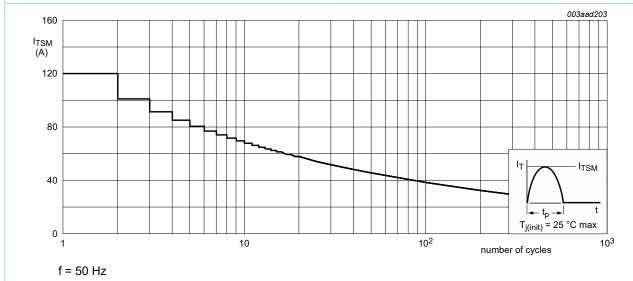


Fig. 4. Non-repetitive peak on-state current as a function of the number of sinusoidal current cycles; maximum values

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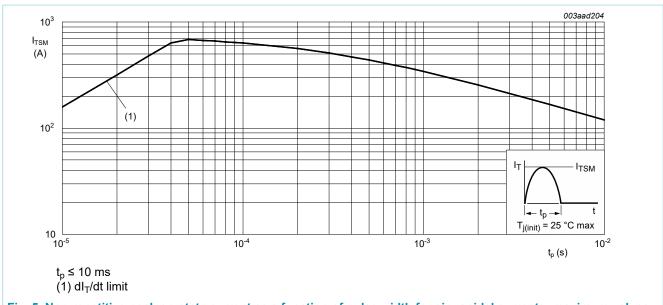
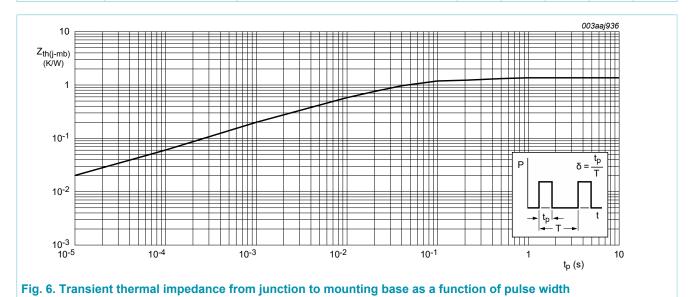


Fig. 5. Non-repetitive peak on-state current as a function of pulse width for sinusoidal currents; maximum values

8. Thermal characteristics

Table 5. Thermal characteristics

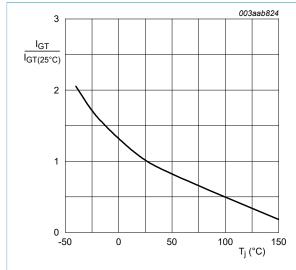
| Symbol | Parameter | Conditions | Min | Тур | Max | Unit |
|-----------------------|--|-------------|-----|-----|-----|------|
| R _{th(j-mb)} | thermal resistance from junction to mounting base | Fig. 6 | - | - | 1.3 | K/W |
| R _{th(j-a)} | thermal resistance from junction to ambient free air | in free air | - | 60 | - | K/W |



9. Characteristics

Table 6. Characteristics

| i able 6. Cha | iracteristics | | | | | |
|---------------------|-----------------------------------|---|------|-----|------|------|
| Symbol | Parameter | Conditions | Min | Тур | Max | Unit |
| Static chara | acteristics | | | | | |
| I _{GT} | gate trigger current | $V_D = 12 \text{ V}; I_T = 0.1 \text{ A}; T_j = 25 \text{ °C}; Fig. 7$ | - | 2 | 15 | mA |
| IL | latching current | $V_D = 12 \text{ V}; I_G = 0.1 \text{ A}; T_j = 25 ^{\circ}\text{C}; Fig. 8$ | - | 10 | 40 | mA |
| I _H | holding current | V _D = 12 V; T _j = 25 °C; <u>Fig. 9</u> | - | 7 | 20 | mA |
| V _T | on-state voltage | I _T = 23 A; T _j = 25 °C; <u>Fig. 10</u> | - | 1.4 | 1.75 | V |
| V_{GT} | gate trigger voltage | $V_D = 12 \text{ V}; I_T = 0.1 \text{ A}; T_j = 25 \text{ °C};$ Fig. 11 | - | 0.6 | 1 | V |
| | | $V_D = 1000 \text{ V}; I_T = 0.1 \text{ A}; T_j = 150 \text{ °C};$ Fig. 11 | 0.25 | 0.4 | - | V |
| I _D | off-state current | V _D = 1000 V; T _j = 150 °C | - | 0.5 | 2.5 | mA |
| I _R | reverse current | V _R = 1000 V; T _j = 150 °C | - | 0.5 | 2.5 | mA |
| Dynamic ch | naracteristics | | | | | |
| dV _D /dt | rate of rise of off-state voltage | V_{DM} = 670 V; T_j = 150 °C; (V_{DM} = 67% of V_{DRM}); exponential waveform; gate open circuit; Fig. 12 | - | 300 | - | V/µs |
| t _{gt} | gate-controlled turn-on time | I_{TM} = 40 A; V_D = 1000 V; I_G = 0.1 A; dI_G/dt = 5 A/ μ s; T_j = 25 °C | - | 2 | - | μs |
| t _q | commutated turn-off time | V_{DM} = 670 V; T_j = 150 °C; I_{TM} = 20 A; V_R = 25 V; $(dI_T/dt)_M$ = 30 A/µs; dV_D/dt = 50 V/µs; $R_{GK(ext)}$ = 100 Ω ; $(V_{DM}$ = 67% of $V_{DRM})$ | - | 70 | - | μs |





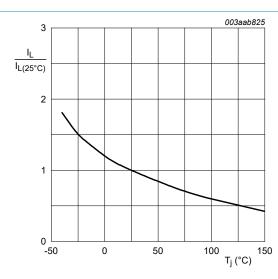


Fig. 8. Normalized latching current as a function of junction temperature

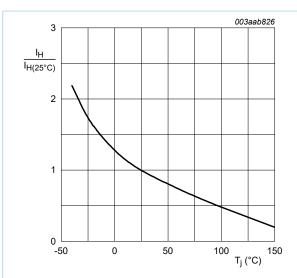
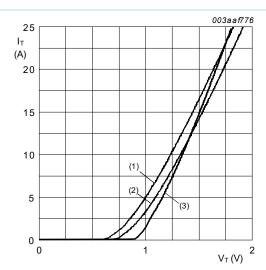


Fig. 9. Normalized holding current as a function of junction temperature



Vo = 0.825 V; Rs = 0.41 Ω

(1) Tj = 150°C; typical values

(2) Tj = 150°C; maximum values

(3) Tj = 25°C; maximum values

Fig. 10. On-state current as a function of on-state voltage

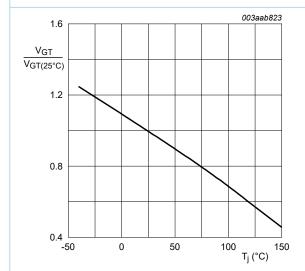


Fig. 11. Normalized gate trigger voltage as a function of junction temperature

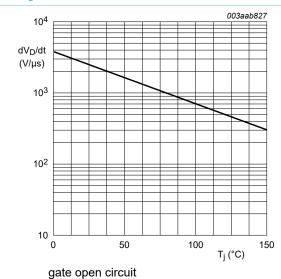
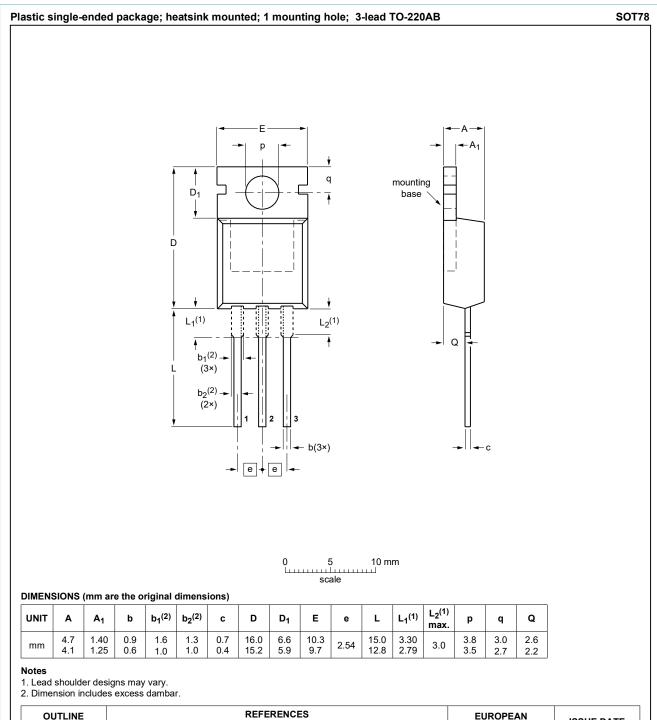


Fig. 12. Critical rate of rise of off-state voltage as a function of junction temperature; typical values

10. Package outline



| VERSION IEC JEDEC JEITA PROJECTION ISSUE DATE SOT78 3-lead TO-220AB SC-46 \$\frac{08-04-23}{08-06-13}\$ 08-04-23-08-06-13 | OUTLINE | | REFER | ENCES | EUROPEAN | ISSUE DATE | |
|--|---------|-----|-----------------|-------|------------|------------|--|
| 1 SO1/8 1 2 Iood TO 2200B SC-46 1 Iood TO 2200B SC-46 Iood TO 2200B SC-46 Iood TO 2200B Iood TO 2200 | VERSION | IEC | JEDEC | JEITA | PROJECTION | ISSUE DATE | |
| | SOT78 | | 3-lead TO-220AB | SC-46 | | | |

Fig. 13. Package outline TO-220AB (SOT78)

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11. Legal information

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| Document status [1][2] | Product status [3] | Definition |
|--------------------------------------|--------------------|---|
| Objective [short] data sheet | Development | This document contains data from the objective specification for product development. |
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